Wuxi Unigroup Microelectronics CO.,LTD.

20V N-Channel Trench MOSFET(Preliminary)

General Description

- Trench Power technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- Optimized for fast-switching applications

Applications

- Synchronous Rectification in DC/DC and AC/DC Converters
- Isolated DC/DC Converters in Telecom and Industrial

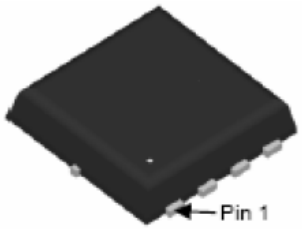
Product Summary

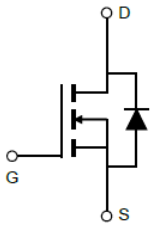
V_{DS}	20V
I_D (at V_{GS}=10V)	120A
$R_{DS(ON)}$ (at V_{GS}=10V)	< 3.4mΩ
$R_{DS(ON)}$ (at V_{GS}=4.5V)	< 3.8mΩ
$R_{DS(ON)}$ (at V_{GS}=2.5V)	< 5.1mΩ

100% UIS Tested

RoHS

DFN3.3x3.3





Part Number	Package Type	Form	Marking
TTG120N02GT	DFN3.3x3.3	Tape&Reel	120N02GT

Absolute Maximum Ratings (T_A =25°C unless otherwise noted)

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current [B]	T_C =25°C	I_D	17	A
	T_C =100°C		17	
Pulsed Drain Current [A]		I_{DM}	360	A
Avalanche Current [A]		I_{AS}	26	A
Single Pulse Avalanche Energy L =0.3mH [A]		E_{AS}	101	mJ
Power Dissipation [C]	T_C =25°C	P_D	108	W
	T_C =100°C		54.3	W
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 175	°C

Thermal Characteristics

Parameter		Symbol	Maximum	Units
Maximum Junction-to-Case	Steady-State	$R_{\theta JC}$	1.38	°C/W
Maximum Junction-to-Ambient	Steady-State	$R_{\theta JA}$	100	

Electrical Characteristics(T_J =25ºC unless otherwise noted)

Symbol	Parameter	Conditions		Value			Units
				Min	Typ	Max	
STATIC PARAMETERS							
BV_{DSS}	Drain-Source Breakdown Voltage	I_D =250μA,V_{GS} =0V		20			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} =20V, V_{GS} =0V	T_J =25ºC			1	μA
			T_J =100ºC			25	
I_{GSS}	Gate-Body Leakage Current	V_{DS} =0V, V_{GS} =±20V				±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} =V_{GS}, I_D =250μA		0.5	0.7	1.2	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS} =10V, I_D =30A			2.6	3.4	mΩ
		V_{GS} =4.5V, I_D =30A			2.9	3.8	mΩ
		V_{GS} =2.5V, I_D =30A			3.9	5.1	mΩ
g_{FS}	Forward Transconductance	V_{DS} =10V, I_D =20A			15		S
V_{SD}	Diode Forward Voltage	I_S =50A, V_{GS} =0V				1	V
I_S	Maximum Body-Diode Continuous Current [B]					17	A
DYNAMIC PARAMETERS							
C_{iss}	Input Capacitance	V_{GS} =0V, V_{DS} =10V, f =1MH_Z			4066		pF
C_{oss}	Output Capacitance				1107		
C_{rss}	Reverse Transfer Capacitance				655		
SWITCHING PARAMETERS							
Q_g(10V)	Total Gate Charge	V_{GS} =10V,V_{DS} =10V, I_D =50A			118		nC
Q_{gs}	Gate Source Charge				7		
Q_{gd}	Gate Drain Charge				22		
$t_{D(on)}$	Turn-On Delay Time	V_{GS} =10V,V_{DS} =10V, I_D =50A, R_G =3Ω			12		ns
t_r	Turn-On Rise Time				11		
$T_{D(off)}$	Turn-Off Delay Time				39		
t_f	Turn-Off Fall Time				18		
t_{rr}	Body Diode Reverse Recovery Time	I_F =50A, di/dt =100A/μs			19		ns
Q_{rr}	Body Diode Reverse Recovery Charge				17		nC

A. Single pulse width limited by maximum junction temperature.

B. The maximum current rating is package limited.

C. The power dissipation P_D is based on $T_{J(MAX)}$ =175ºC, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

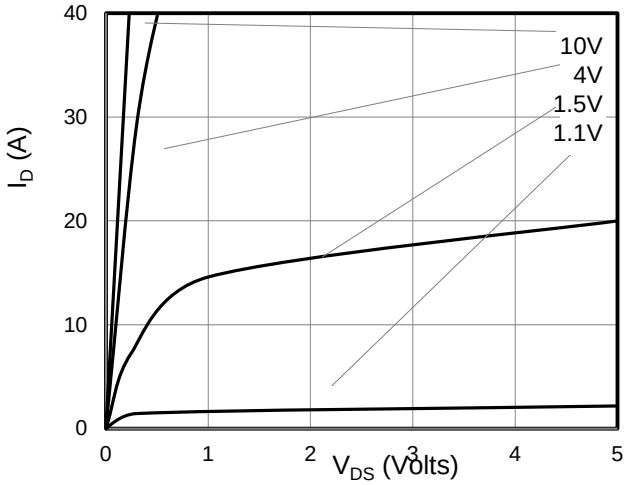


Figure 1: On-Region Characteristics

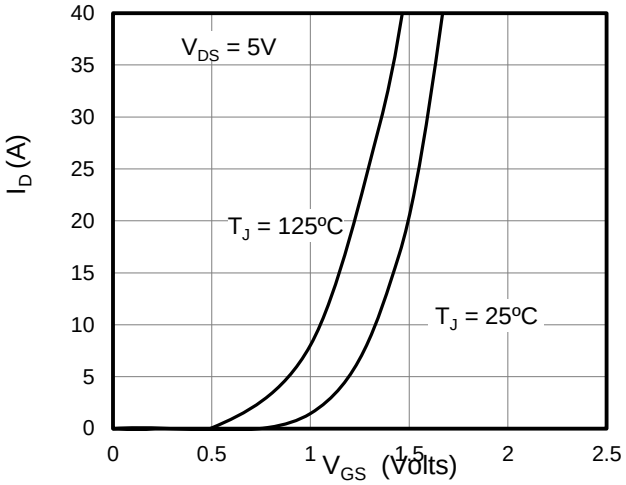


Figure 2: Transfer Characteristics

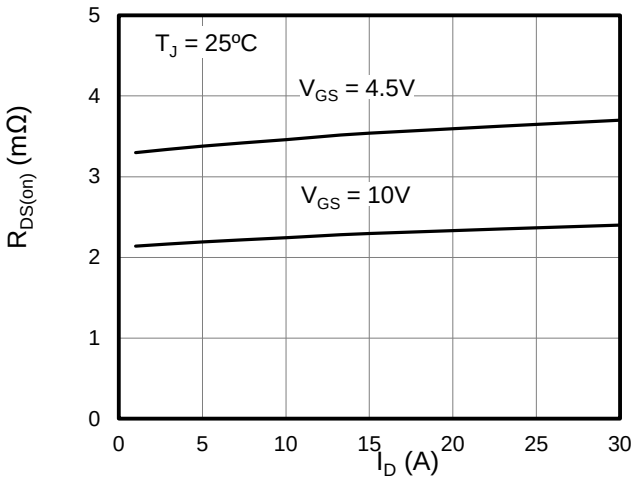


Figure 3: On-Resistance vs. Drain Current

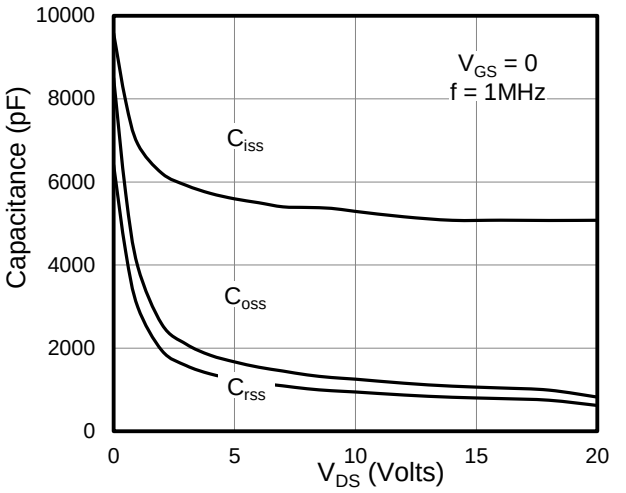


Figure 4: Capacitance Characteristics

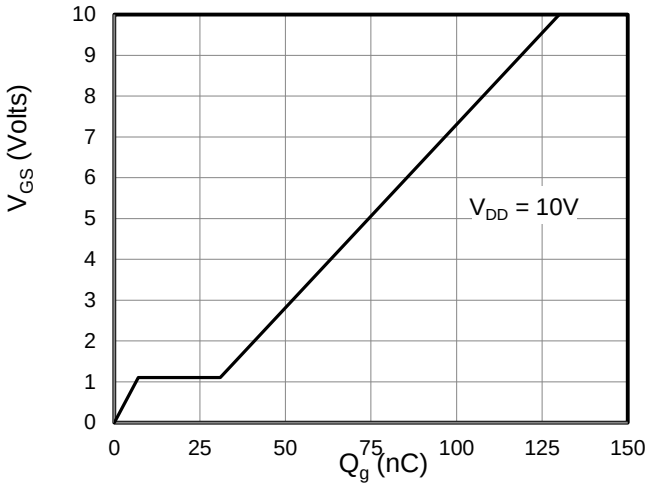


Figure 5: Gate Charge Characteristics

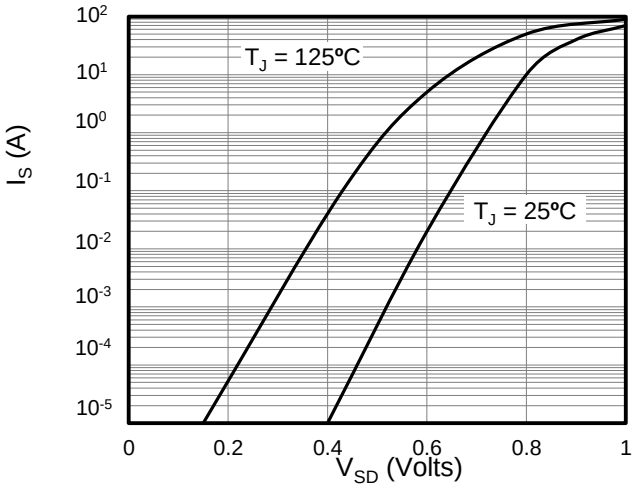


Figure 6: Body Diode Forward Voltage

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

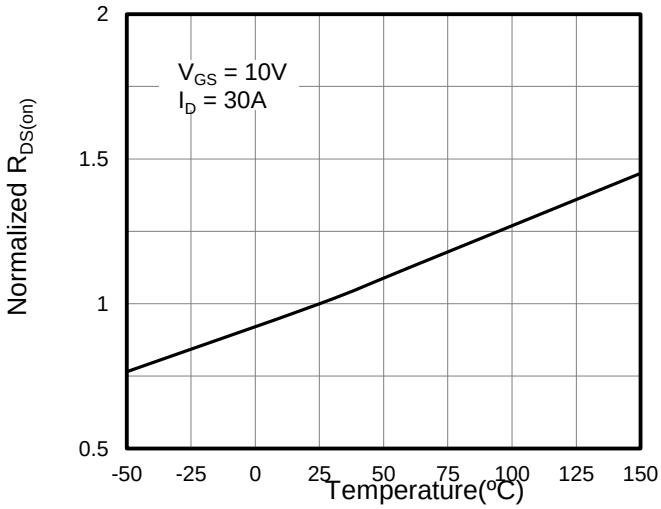


Figure 7: On-Resistance vs. Junction Temperature

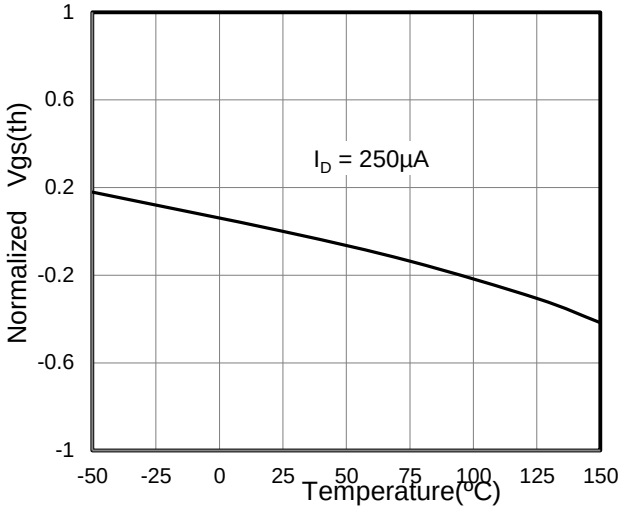


Figure 8: Vgs(th) vs. Junction Temperature

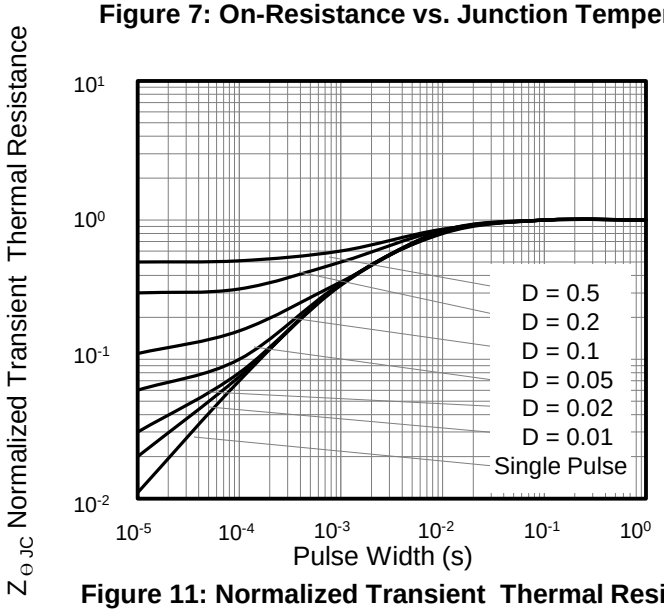


Figure 11: Normalized Transient Thermal Resistance

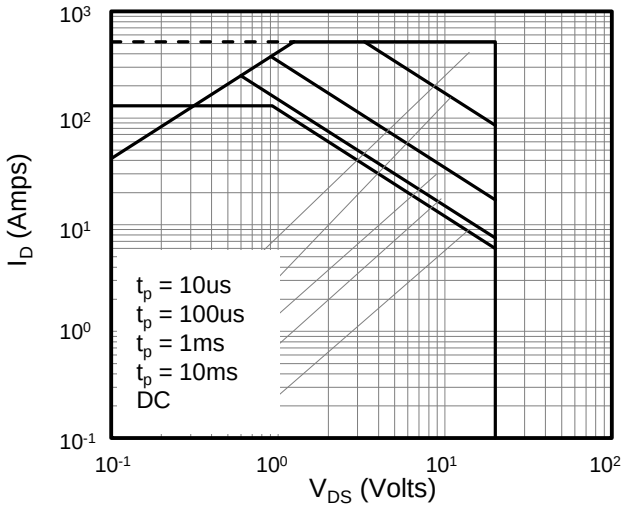


Figure 12: Safe Operating Area

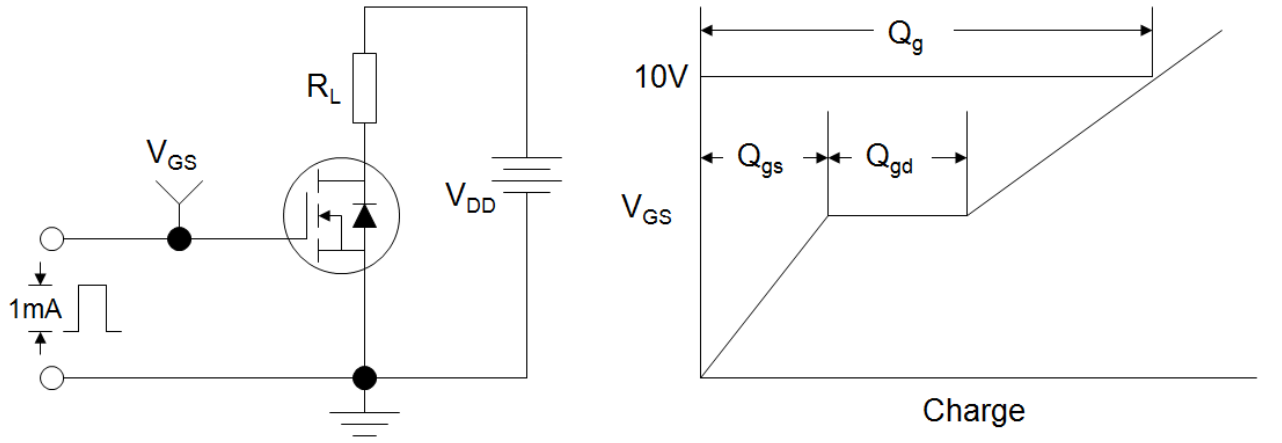


Figure A：Gate Charge Test Circuit and Waveforms

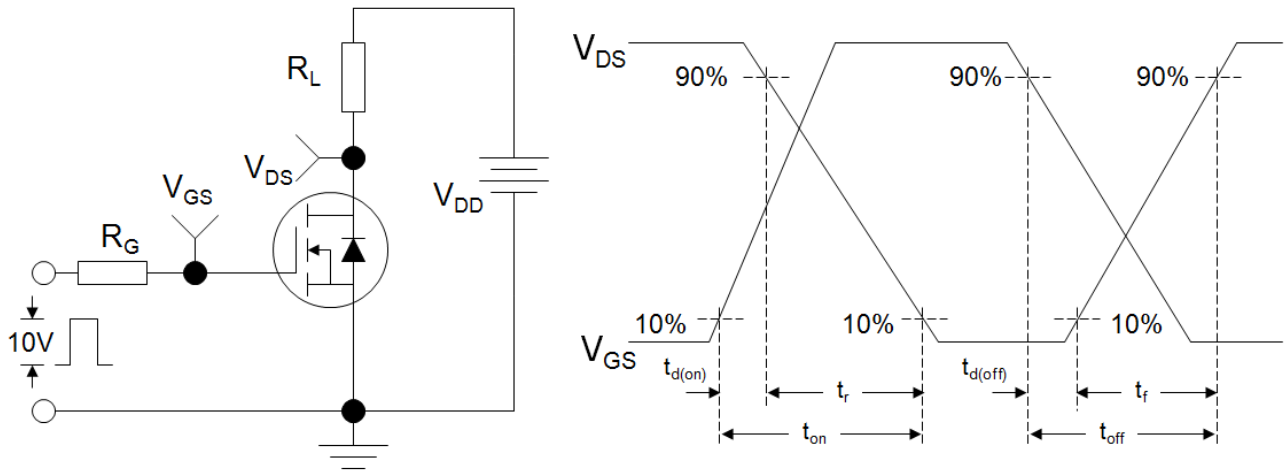


Figure B：Resistive Switching Test Circuit and Waveforms

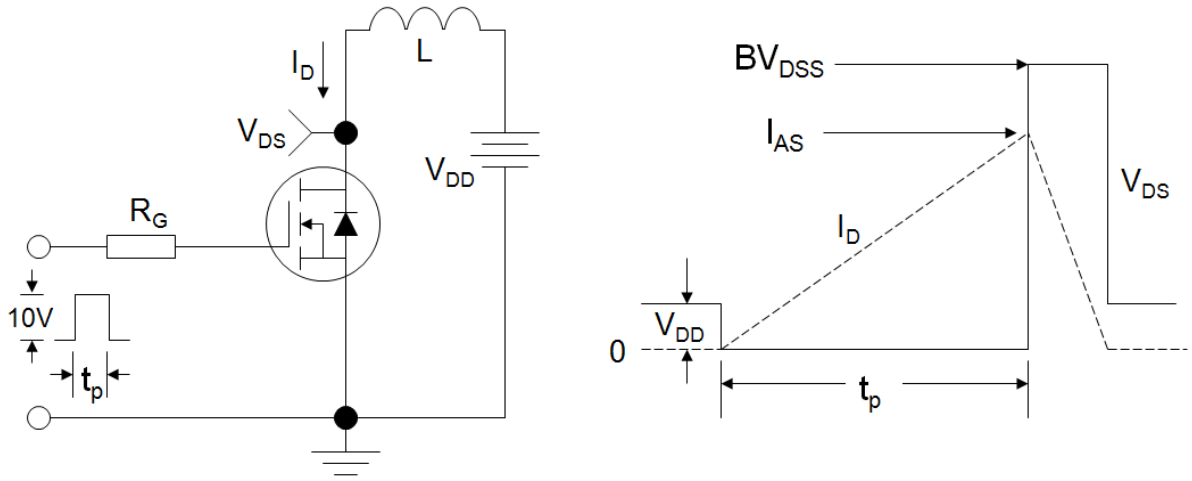
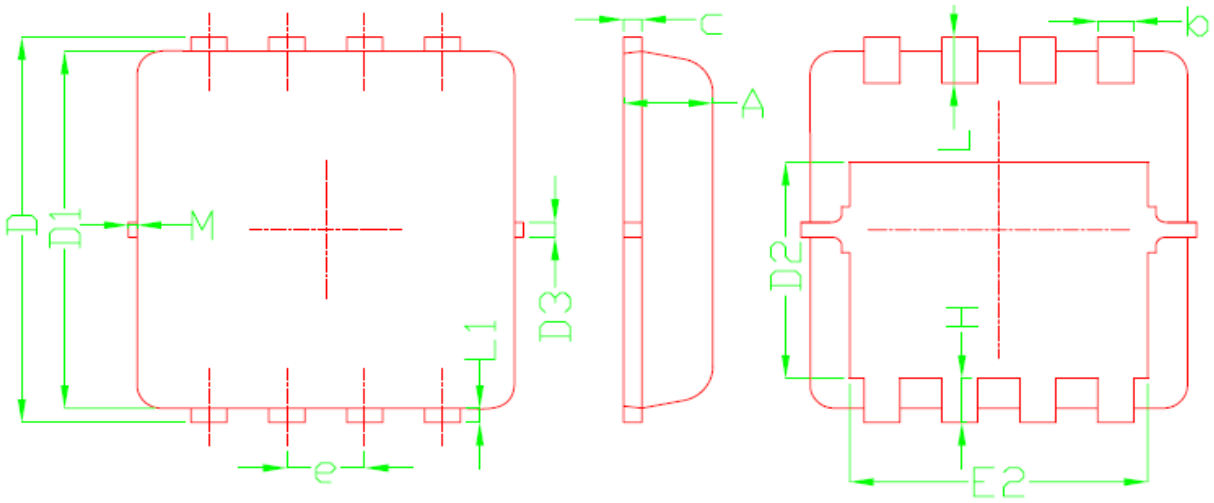
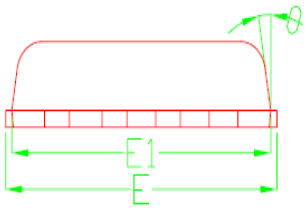
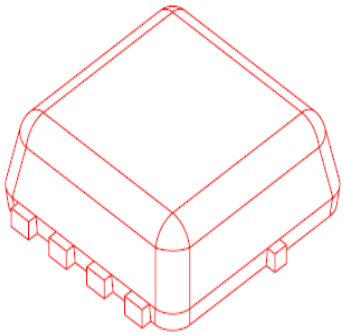


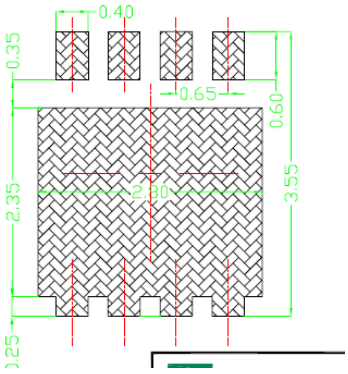
Figure C：Unclamped Inductive Switching (UIS) Test Circuit and Waveforms

DFN 3.3x3.3









SYMBOL	DIMENSIONAL REQMTS		
	MIN	NOM	MAX
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.78	1.88	1.98
D3	---	0.13	---
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	---	0.13	---
θ	---	10°	12°
M	*	*	0.15
* Not specified			

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